



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hideomi Suzawa et al.      Art Unit : 2812  
Serial No. : 09/852,672      Examiner : Viktor Simkovic  
Filed : May 11, 2001      Confirmation No. 5083  
Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Commissioner for Patents  
Washington, D.C. 20231

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**RESPONSE TO OFFICE ACTION**

In response to the action mailed June 19, 2002, please amend the application as follows:

In the claims:

**Please cancel claims 1-8 without prejudice or disclaimer.**

**Please amend claims 28 and 33 as follows:**

-- 28. (Amended) A method of manufacturing a semiconductor device comprising steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

laminating a first conductive film and a second conductive film on said insulating film;

forming a second conductive layer with a first width;

adding an impurity element to said semiconductor layer using said second conductive layer with said first width as a mask to form a high concentration impurity region;

etching said first conductive film to form a first electrode comprising a laminate structure of a first conductive layer with a second width and said second conductive layer with a third width;

etching said second conductive layer to form a second electrode comprising a laminate structure of said first conductive layer with said second width and said second conductive layer with a fourth width;